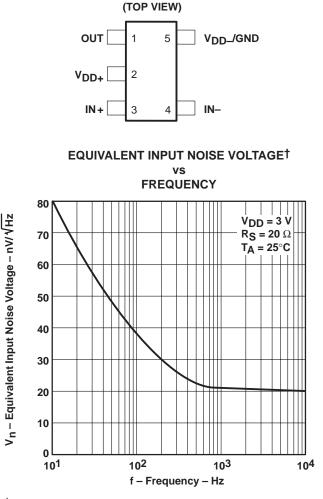
DBV PACKAGE

- Output Swing Includes Both Supply Rails
- Low Noise . . . 21 nV/ \sqrt{Hz} Typ at f = 1 kHz
- Low Input Bias Current . . . 1 pA Typ
- Very Low Power . . . 11 μA Per Channel Typ
- Common-Mode Input Voltage Range Includes Negative Rail
- Wide Supply Voltage Range 2.7 V to 10 V
- Available in the SOT-23 Package
- Macromodel Included

description

The TLV2711 is a single low-voltage operational amplifier available in the SOT-23 package. It consumes only 11 μ A (typ) of supply current and is ideal for battery-power applications. Looking at Figure 1, the TLV2711 has a 3-V noise level of 21 nV/ $\sqrt{\text{Hz}}$ at 1 kHz; five times lower than competitive SOT-23 micropower solutions. The device exhibits rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV2711 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2711, exhibiting high input impedance and low noise, is excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs).



[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

Figure 1. Equivalent Input Noise Voltage Versus Frequency

With a total area of 5.6mm², the SOT-23 package only requires one-third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces.

т.	Viemov AT 25°C	PACKAGED DEVICES	SYMBOL	CHIP FORM [‡]							
TA	V _{IO} max AT 25°C	SOT-23 (DBV)†	STWBOL	(Y)							
0°C to 70°C	3 mV	TLV2711CDBV	VAJC	TI V2711Y							
-40°C to 85°C	3 mV	TLV2711IDBV	VAJI								

AVAILABLE OPTIONS

[†] The DBV package available in tape and reel only.

[‡]Chip forms are tested at $T_A = 25^{\circ}C$ only.



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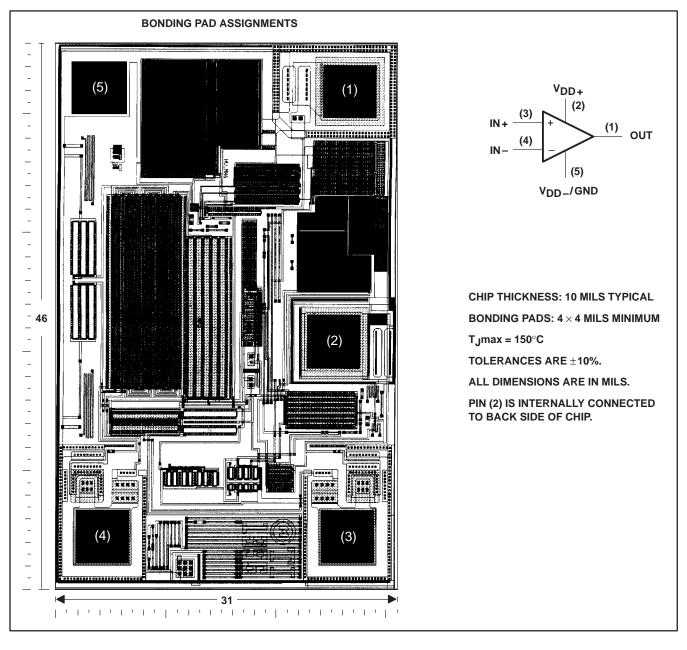


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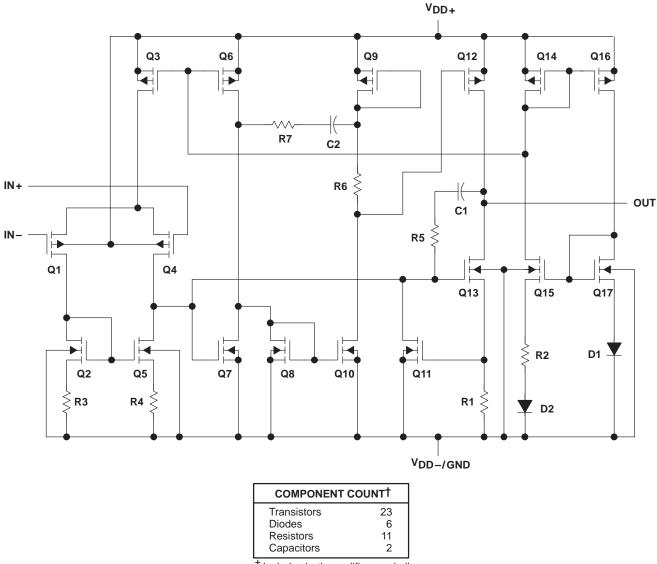
TLV2711Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2711C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.





equivalent schematic



[†] Includes both amplifiers and all ESD, bias, and trim circuitry



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage, V _{ID} (see Note 2)	
Input voltage range, V _I (any input, see Note 1)	–0.3 V to V _{DD}
Input current, I _I (each input)	±5 mA
Output current, I _O	±50 mA
Total current into V _{DD+}	±50 mA
Total current out of V _{DD}	±50 mA
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A : TLV2711C	0°C to 70°C
	–40°C to 85°C
Storage temperature range, T _{stg}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV pac	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD} -.

 Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below V_{DD} – 0.3 V.

3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C	POWER RATING	POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

recommended operating conditions

	TL	.V2711C	TI	UNIT	
	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD} (see Note 1)	2.7	10	2.7	10	V
Input voltage range, VI	V _{DD} -	V _{DD+} -1.3	V _{DD} -	V _{DD+} -1.3	V
Common-mode input voltage, VIC	V _{DD} -	V _{DD+} -1.3	V _{DD} -	V _{DD+} -1.3	V
Operating free-air temperature, T _A	0	70	-40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD}_.



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electrical characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

		TEOT OOND			Т	LV2711	С		FLV2711	I	
	PARAMETER	TEST COND	ITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
VIO	Input offset voltage					0.4	3		0.4	3	mV
αΛΙΟ	Temperature coefficient of input offset voltage			Full range		1			1		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 1.5 V,$ $V_{O} = 0,$	$V_{IC} = 0,$ R _S = 50 Ω	25°C		0.003			0.003		μV/m
10	Input offset current			25°C		0.5	60		0.5	60	
10				Full range			150			150	pА
IB	Input bias current			25°C			60			60	P.1
				Full range		1	150		1	150	
\ <i>\</i>	Common-mode input		D- 50.0	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
VICR	voltage range	V _{IO} ≤5 mV,	R _S = 50 Ω	Full range	0 to 1.7			0 to 1.7			V
		I _{OH} = -100 μA		25°C		2.94			2.94		
Vон	High-level output voltage	L 050 A		25°C		2.85			2.85		V
	vollage	I _{OH} = -250 μA		Full range	2.6			2.6			
		V _{IC} = 1.5 V,		25°C		15			15		
VOL	Low-level output voltage	V _{IC} = 1.5 V,	I _{OL} = 500 μA	25°C		150			150		mV
	voltago	VIC = 1.5 V,	IOL = 300 μA	Full range			500			500	
	Large-signal		R _I = 10 kΩ [‡]	25°C	3	7		3	7		
AVD	differential voltage	$V_{IC} = 1.5 V,$ $V_{O} = 1 V \text{ to } 2 V$	KL = 10 K22+	Full range	1			1			۷/m۱
	amplification	6	$R_L = 1 M\Omega^{\ddagger}$	25°C		600			600		
ri(d)	Differential input resistance			25°C		10 ¹²			10 ¹²		Ω
^r i(c)	Common-mode input resistance			25°C		1012			1012		Ω
^C i(c)	Common-mode input capacitance	f = 10 kHz,		25°C		5			5		pF
z _o	Closed-loop output impedance	f = 7 kHz,	A _V = 1	25°C		200			200		Ω
CMRR	Common-mode		V _O = 1.5 V,	25°C	65	83		65	83		dB
	rejection ratio	R _S = 50 Ω		Full range	60			60			uВ
ksvr	Supply voltage rejection ratio	$V_{DD} = 2.7 \text{ V to 8 V},$	$V_{IC} = V_{DD}/2$	25°C	80	95		80	95		dB
	$(\Delta V_{DD} / \Delta V_{IO})$	No load	3	Full range	80			80			
	Supply current	V _O = 1.5 V,	No load	25°C		11	25		11	25	μA
DD	oupply current	VU = 1.5 V,	NU IUdu	Full range			30			30	μΑ

[†] Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is – 40°C to 85°C.

‡Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to $T_A = 25^{\circ}C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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operating characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

				-						
	TEST COND		. . +	Т	LV2711	C	1	LV2711	I	UNIT
FARAMETER	TEST COND	'A'	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
		B. 10 kot	25°C	0.01	0.025		0.01	0.025		
Slew rate at unity gain	$C_{L} = 100 \text{ pF}^{\ddagger}$	Full range	0.005			0.005			V/µs	
Equivalent input noise	f = 10 Hz		25°C		80			80		
voltage	f = 1 kHz		25°C		22			22		nV/√Hz
Peak-to-peak equivalent	f = 0.1 Hz to 1 Hz		25°C		660			660		nV
input noise voltage	f = 0.1 Hz to 10 Hz	Hz to 10 Hz			880			880		ΠV
Equivalent input noise current			25°C		0.6			0.6		fA/√Hz
Gain-bandwidth product	f = 10 kHz, C _L = 100 pF [‡]	$R_L = 10 \text{ k}\Omega^{\ddagger}$,	25°C		56			56		kHz
Maximum output-swing bandwidth	VO(PP) = 1 V, R _L = 10 kΩ [‡] ,	A _V = 1, C _L = 100 pF‡	25°C		7			7		kHz
Phase margin at unity gain	R _L = 10 kه,	C _L = 100 pF‡	25°C		56°			56°		
Gain margin		_	25°C		20			20		dB
	Equivalent input noise voltage Peak-to-peak equivalent input noise voltage Equivalent input noise current Gain-bandwidth product Maximum output-swing bandwidth Phase margin at unity gain	Slew rate at unity gain $V_O = 1.1 V \text{ to } 1.9 V,$ $C_L = 100 pF^{\ddagger}$ Equivalent input noise voltage $f = 10 \text{ Hz}$ $f = 1 \text{ kHz}$ Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz} \text{ to } 1 \text{ Hz}$ $f = 0.1 \text{ Hz} \text{ to } 10 \text{ Hz}$ Equivalent input noise current $f = 0.1 \text{ Hz} \text{ to } 10 \text{ Hz}$ $f = 0.1 \text{ Hz} \text{ to } 10 \text{ Hz}$ Equivalent input noise current $f = 10 \text{ kHz},$ $C_L = 100 \text{ pF}^{\ddagger}$ Maximum output-swing bandwidth $VO(PP) = 1 V,$ $R_L = 10 \text{ k}\Omega^{\ddagger},$ Phase margin at unity gain $R_L = 10 \text{ k}\Omega^{\ddagger},$	Slew rate at unity gain $V_O = 1.1 \vee \text{to} 1.9 \vee, C_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 10 \text{ k}\Omega^{\ddagger}, R_L = 10 \text{ k}\Omega^{\ddagger}, R_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 10 \text{ k}\Omega^{\ddagger}, R_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 100 \text$	Slew rate at unity gain $V_O = 1.1 \vee to 1.9 \vee, C_L = 100 \mu \text{F}^{\ddagger}$ $R_L = 10 \mu \Omega^{\ddagger}, \Omega^{\ddagger}$ 25°C Slew rate at unity gain $f = 10 \text{ Hz}$ 25°C Full rangeEquivalent input noise voltage $f = 10 \text{ Hz}$ 25°C Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz}$ to 1 Hz 25°C Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz}$ to 10 Hz 25°C Equivalent input noise current $f = 0.1 \text{ Hz}$ to 10 Hz 25°C Equivalent input noise current $f = 10 \text{ kHz}, C_L = 100 \text{ pF}^{\ddagger}$ 25°C Gain-bandwidth product $f = 10 \text{ kHz}, C_L = 100 \text{ k}\Omega^{\ddagger}, C_L = 100 \text{ pF}^{\ddagger}$ 25°C Maximum output-swing bandwidth $VO(PP) = 1 \text{ V}, A_V = 1, C_L = 100 \text{ pF}^{\ddagger}$ 25°C Phase margin at unity gain $R_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 100 \text{ pF}^{\ddagger}$ 25°C	PARAMETERTEST CONDITIONSTATSlew rate at unity gain $V_O = 1.1 V \text{ to } 1.9 V, C_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 10 \text{ k}\Omega^$	PARAMETERTEST CONDITIONSTA [†] MINTYPSlew rate at unity gain $V_O = 1.1 V \text{ to } 1.9 V, C_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 100 \text{ pF}^{\ddagger}$ $25^{\circ}C$ 0.01 0.025 Slew rate at unity gain $f = 10 \text{ Hz}$ $25^{\circ}C$ $Full range$ 0.005 $Full range$ 0.005 Equivalent input noise voltage $f = 10 \text{ Hz}$ $25^{\circ}C$ $22^{\circ}C$ 80 Peak-to-peak equivalent input noise voltage $f = 0.1 \text{ Hz} \text{ to } 1 \text{ Hz}$ $25^{\circ}C$ 660 Equivalent input noise voltage $f = 0.1 \text{ Hz} \text{ to } 10 \text{ Hz}$ $25^{\circ}C$ 660 Equivalent input noise current $f = 0.1 \text{ Hz} \text{ to } 10 \text{ Hz}$ $25^{\circ}C$ 660 Gain-bandwidth product $f = 10 \text{ kHz}, C_L = 100 \text{ pF}^{\ddagger}$ $25^{\circ}C$ 0.6 Maximum output-swing bandwidth $VO(PP) = 1 V, AV = 1, C_L = 100 \text{ pF}^{\ddagger}$ $25^{\circ}C$ 7 Phase margin at unity gain $R_L = 10 \text{ k}\Omega^{\ddagger}, C_L = 100 \text{ pF}^{\ddagger}$ $25^{\circ}C$ 56°	Slew rate at unity gain $V_O = 1.1 \vee to 1.9 \vee V_C = 10 \ \mu L^2$ $R_L = 10 \ \mu \Omega^2$ $25^\circ C$ 0.01 0.025 Equivalent input noise voltage $f = 10 \ Hz$ $25^\circ C$ $25^\circ C$ 80 Peak-to-peak equivalent input noise voltage $f = 0.1 \ Hz$ to $1 \ Hz$ $25^\circ C$ $25^\circ C$ 80 Equivalent input noise voltage $f = 0.1 \ Hz$ to $10 \ Hz$ $25^\circ C$ 80 80 Equivalent input noise voltage $f = 0.1 \ Hz$ to $10 \ Hz$ $25^\circ C$ 80 80 Equivalent input noise current $f = 0.1 \ Hz$ to $10 \ Hz$ $25^\circ C$ 80 80 Gain-bandwidth product $f = 10 \ Hz, C_L = 100 \ pF^{\ddagger}$ $R_L = 10 \ \mu\Omega^{\ddagger}, C_L = 100 \ pF^{\ddagger}$ $25^\circ C$ 56 Maximum output-swing bandwidth $VO(PP) = 1 \ V, R_L = 10 \ \mu\Omega^{\ddagger}, C_L = 100 \ pF^{\ddagger}$ $25^\circ C$ 7 Phase margin at unity gain $R_L = 10 \ \mu\Omega^{\ddagger}, C_L = 100 \ pF^{\ddagger}$ $25^\circ C$ 56° 76°	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

[†] Full range is -40° C to 85° C.

‡Referenced to 1.5 V



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	DADAMETED	TEAT OOND	TIONO	- +	Т	LV2711	С	-	FLV2711	I	
	PARAMETER	TEST COND	IIIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
VIO	Input offset voltage					0.45	3		0.45	3	mV
αNO	Temperature coefficient of input offset voltage			Full range		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 2.5 V,$ $V_{O} = 0,$	$V_{IC} = 0,$ R _S = 50 Ω	25°C		0.003			0.003		μV/mo
10	Input offset current			25°C		0.5	60		0.5	60	pА
10	input onset sument			Full range			150			150	p/1
IВ	Input bias current			25°C		1	60		1	60	pА
.ID				Full range			150			150	p
	Common-mode input		D 50.0	25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2		V
VICR	voltage range	V _{IO} ≤5 mV	R _S = 50 Ω	Full range	0 to 3.5			0 to 3.5			V
		I _{OH} = -100 μA		25°C		4.95			4.95		
Vон	High-level output voltage			25°C		4.875			4.875		V
	vollage	I _{OH} = -250 μA		Full range	4.6			4.6			
		V _{IC} = 2.5 V,		25°C		12			12		
VOL	Low-level output voltage		La. 500 HA	25°C		120			120		mV
	· • · · · · · · · · · · · · · · · · · ·	V _{IC} = 2.5 V,	I _{OL} = 500 μA	Full range			500			500	
	Large-signal		$R_{I} = 10 k\Omega^{\ddagger}$	25°C	6	12		6	12		
AVD	differential	$V_{IC} = 2.5 V,$ $V_{O} = 1 V \text{ to } 4 V$	_	Full range	3			3			V/m∖
	voltage amplification	6	$R_L = 1 M\Omega^{\ddagger}$	25°C		800			800		
ri(d)	Differential input resistance			25°C		1012			1012		Ω
ri(c)	Common-mode input resistance			25°C		1012			1012		Ω
^c i(c)	Common-mode input capacitance	f = 10 kHz,		25°C		5			5		pF
z _o	Closed-loop output impedance	f = 7 kHz,	A _V = 1	25°C		200			200		Ω
CMRR	Common-mode	$V_{IC} = 0$ to 2.7 V,	V _O = 2.5 V,	25°C	70	83		70	83		dB
	rejection ratio	R _S = 50 Ω		Full range	70			70			uВ
ksvr	Supply voltage rejection ratio	$V_{DD} = 4.4 \text{ V} \text{ to } 8 \text{ V},$ No load	$V_{IC} = V_{DD}/2$,	25°C	80	95		80	95		dB
	$(\Delta V_{DD} / \Delta V_{IO})$			Full range	80			80			
DD	Supply current	V _O = 2.5 V,	No load	25°C		13	25		13	25	μA
טטי	Supply current	v 0 - 2.5 v,	NU IUAU	Full range			30			30	μΑ

[†] Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is – 40°C to 85°C.

‡Referenced to 1.5 V

NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to $T_A = 25^{\circ}C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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operating characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	- +	Т	LV2711	С	ר	LV2711	I	UNIT
	PARAMETER	TEST COND	mons	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
		V _O = 1.5 V to 3.5 V,	B. 10 kot	25°C	0.01	0.025		0.01	0.025		
SR	Slew rate at unity gain	$C_{L} = 100 \text{ pF}^{\ddagger}$	Full range	0.005			0.005			V/µs	
V	Equivalent input noise	f = 10 Hz		25°C		72			72		a) (()] =
Vn	voltage	f = 1 kHz		25°C		21			21		nV/√Hz
Veren	Peak-to-peak equivalent	f = 0.1 Hz to 1 Hz		25°C		600			600		nV
V _{N(PP)}	input noise voltage	f = 0.1 Hz to 10 Hz		25°C		800			800		ΠV
I _n	Equivalent input noise current			25°C		0.6			0.6		fA/√Hz
	Gain-bandwidth product	f = 10 kHz, C _L = 100 pF [‡]	$R_L = 10 \text{ k}\Omega^{\ddagger},$	25°C		65			65		kHz
BOM	Maximum output-swing bandwidth	V _{O(PP)} = 2 V, R _L = 10 kه,	A _V = 1, C _L = 100 pF‡	25°C		7			7		kHz
φm	Phase margin at unity gain	R _L = 10 kه,	C _L = 100 pF‡	25°C		60°			60°		
	Gain margin			25°C		22			22		dB

[†] Full range is -40° C to 85° C.

‡Referenced to 1.5 V

electrical characteristics at V_DD = 3 V, T_A = 25 $^\circ\text{C}$ (unless otherwise noted)

					T	LV2711Y	,	
	PARAMETER		ST CONDITIONS		MIN	TYP	MAX	UNIT
VIO	Input offset voltage					0.47		mV
lio	Input offset current	$V_{DD\pm} = \pm 1.5 V,$ R _S = 50 Ω	$V_{O} = 0,$	$V_{IC} = 0,$		0.5		pА
I _{IB}	Input bias current	113 - 00 12				1		pА
VICR	Common-mode input voltage range	V _{IO} ≤5 mV,	R _S = 50 Ω			-0.3 to 2.2		V
\/		I _{OH} = -100 μA				2.94		V
Vон	High-level output voltage	I _{OH} = -200 μA				2.85		V
Ve	Low-level output voltage	$V_{IC} = 0,$	I _{OL} = 50 μA			15		mV
VOL	Low-level output voltage	$V_{IC} = 0,$	l _{OL} = 500 μA			150		IIIV
A=	Large-signal differential			$R_L = 10 \ k\Omega^{\dagger}$		7		V/mV
AVD	voltage amplification	V _{IC} = 1.5 V,	$V_{O} = 1 V \text{ to } 2 V$	$R_L = 1 M\Omega^{\dagger}$		600		V/IIIV
^r i(d)	Differential input resistance			•		1012		Ω
^r i(c)	Common-mode input resistance					1012		Ω
^C i(C)	Common-mode input capacitance	f = 10 kHz				5		pF
z _o	Closed-loop output impedance	f = 7 kHz,	$A_V = 1$			200		Ω
CMRR	Common-mode rejection ratio	V _{IC} = 0 to 1.7 V,	V _O = 1.5 V,	R _S = 50 Ω		83		dB
k SVR	Supply voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	$V_{DD} = 2.7 V \text{ to } 8 V,$	$V_{IC} = V_{DD}/2$,	No load		95		dB
IDD	Supply current	V _O = 1.5 V,	No load			11		μA

[†]Referenced to 1.5 V



electrical characteristics at V_DD = 5 V, T_A = 25°C (unless otherwise noted)

		TE			Т	LV2711Y	,	
	PARAMETER	IE:	ST CONDITIONS		MIN	TYP	MAX	UNIT
VIO	Input offset voltage					0.45		mV
IIO	Input offset current	$V_{DD} \pm = \pm 2.5 V,$ R _S = 50 Ω	V _{IC} = 0,	VO = 0,		0.5		pА
I _{IB}	Input bias current	113 - 30 32				1		pА
VICR	Common-mode input voltage range	V _{IO} ≤5 mV,	R _S = 50 Ω			-0.3 to 4.2		V
N/		I _{OH} = -100 μA				4.95		V
VOH	High-level output voltage	I _{OH} = -250 μA				4.875		V
Ve		V _{IC} = 2.5 V,	I _{OL} = 50 μA			12		mV
VOL	Low-level output voltage	V _{IC} = 2.5 V,	I _{OL} = 500 μA			120		IIIV
A	Large-signal differential			$R_L = 10 \text{ k}\Omega^{\dagger}$		12		V/mV
AVD	voltage amplification	V _{IC} = 2.5 V,	$V_{O} = 1 V \text{ to } 4 V$	$R_L = 1 M\Omega^{\dagger}$		800		V/IIIV
^r i(d)	Differential input resistance			•		1012		Ω
ri(c)	Common-mode input resistance					1012		Ω
c _{i(c)}	Common-mode input capacitance	f = 10 kHz				5		pF
z ₀	Closed-loop output impedance	f = 7 kHz,	$A_V = 1$			200		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = 0$ to 2.7 V,	V _O = 2.5 V,	R _S = 50 Ω		83		dB
k SVR	Supply voltage rejection ratio $(\Delta V_{DD} / \Delta V_{IO})$	V_{DD} = 4.4 V to 8 V,	$V_{IC} = V_{DD}/2$,	No load		95		dB
I _{DD}	Supply current	V _O = 2.5 V,	No load			13		μA

[†]Referenced to 1.5 V



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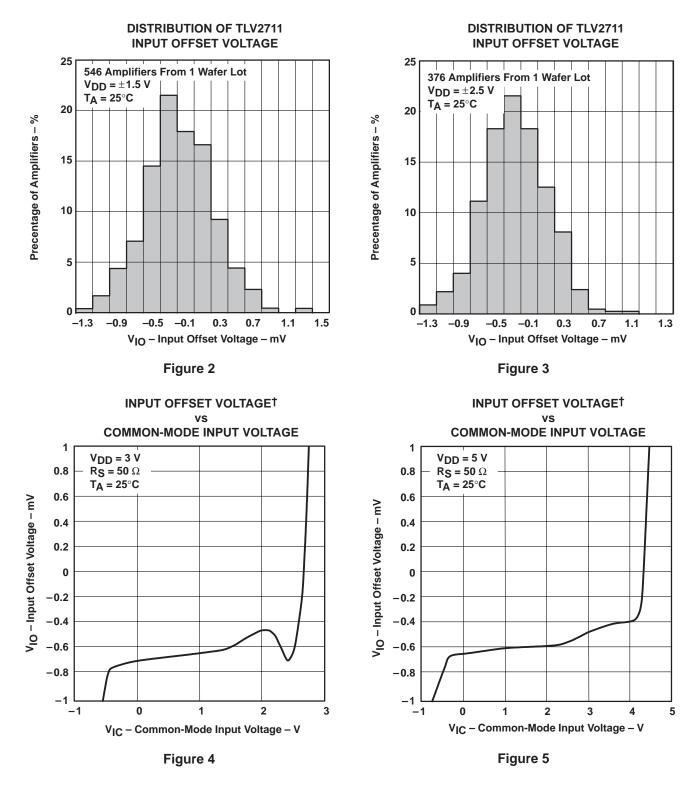
TYPICAL CHARACTERISTICS

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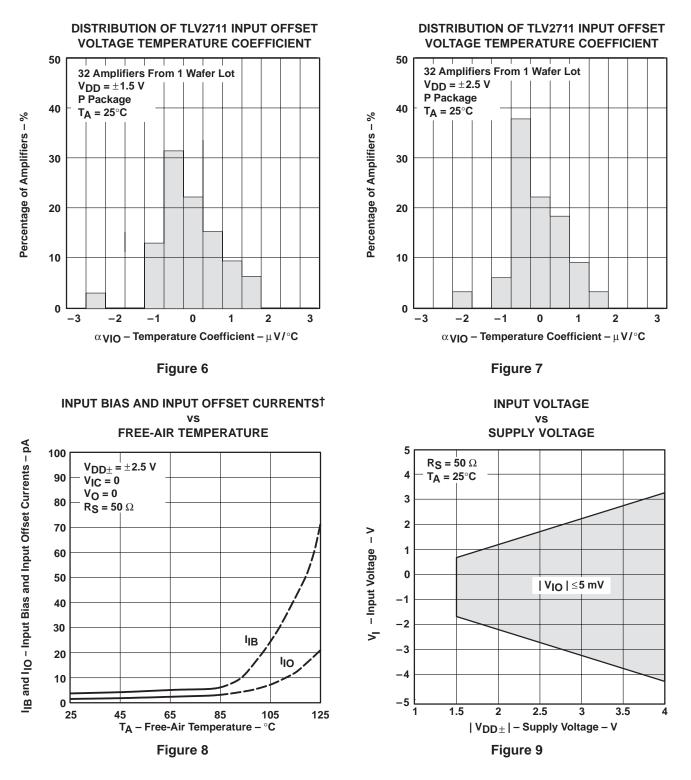
TYPICAL CHARACTERISTICS



[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



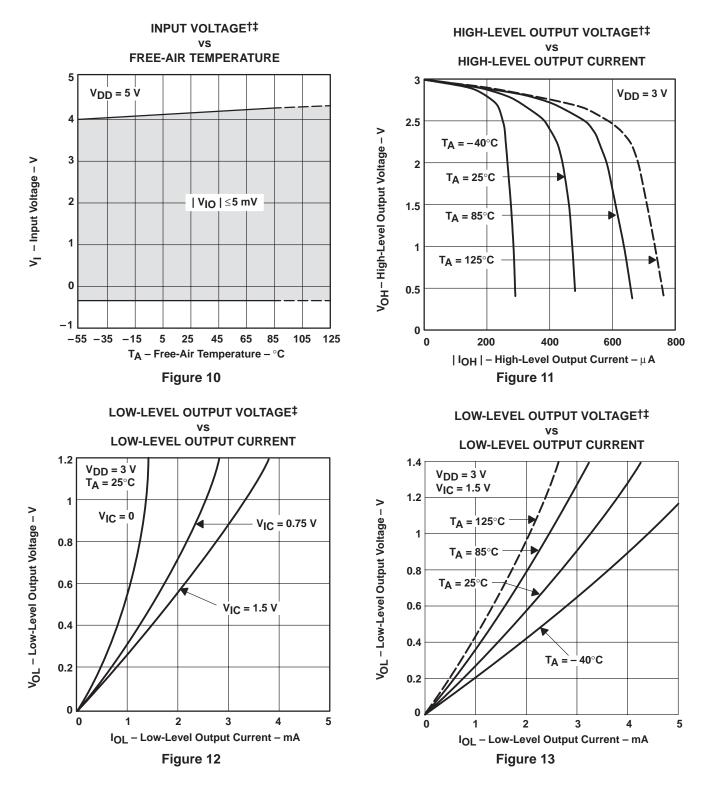
TYPICAL CHARACTERISTICS



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

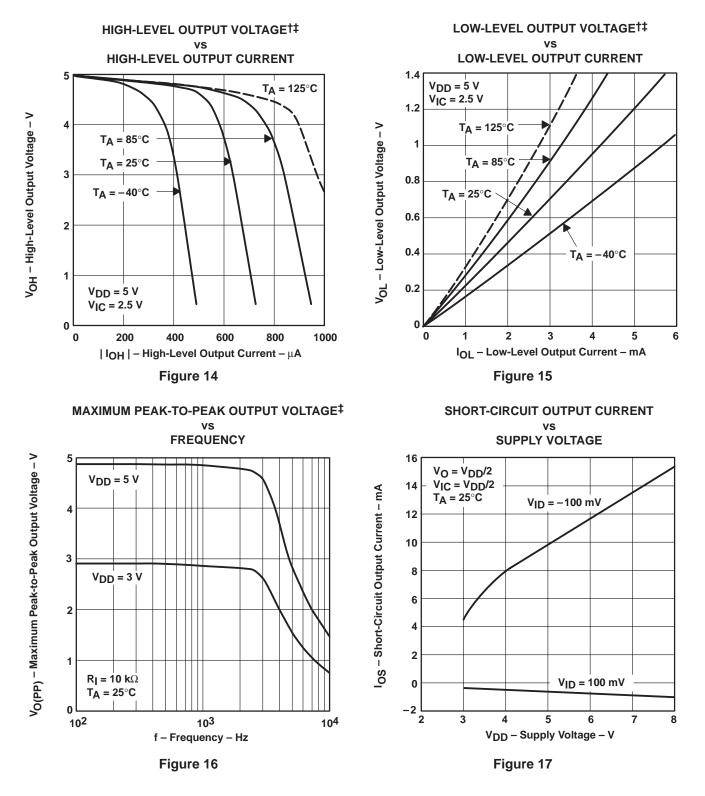


TYPICAL CHARACTERISTICS



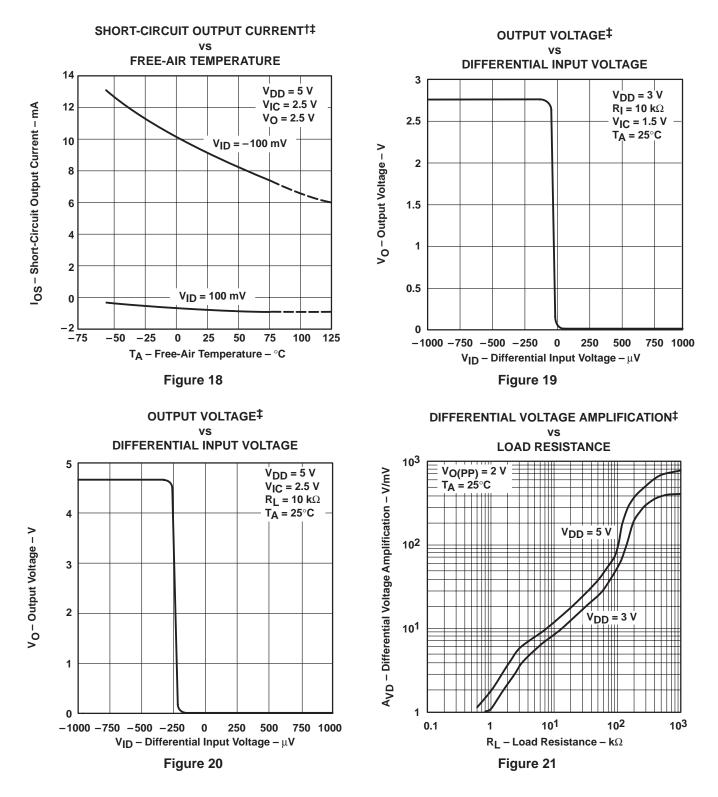


TYPICAL CHARACTERISTICS



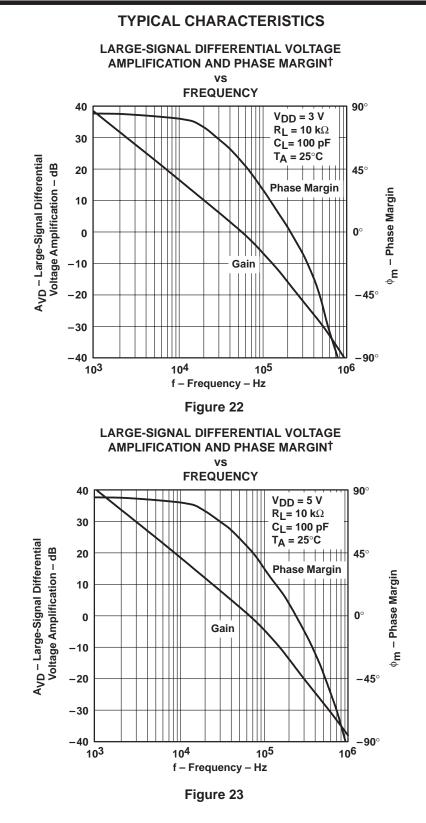


TYPICAL CHARACTERISTICS





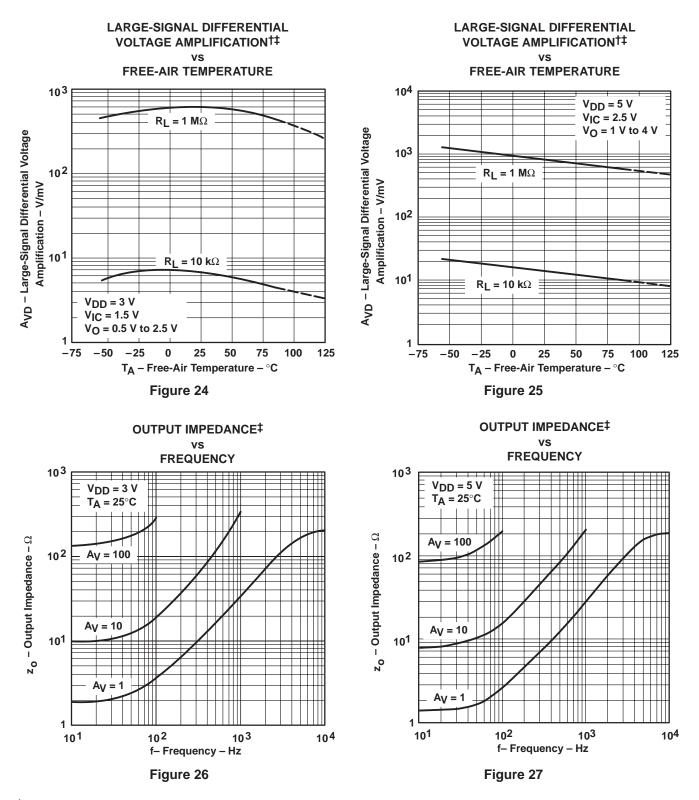
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[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

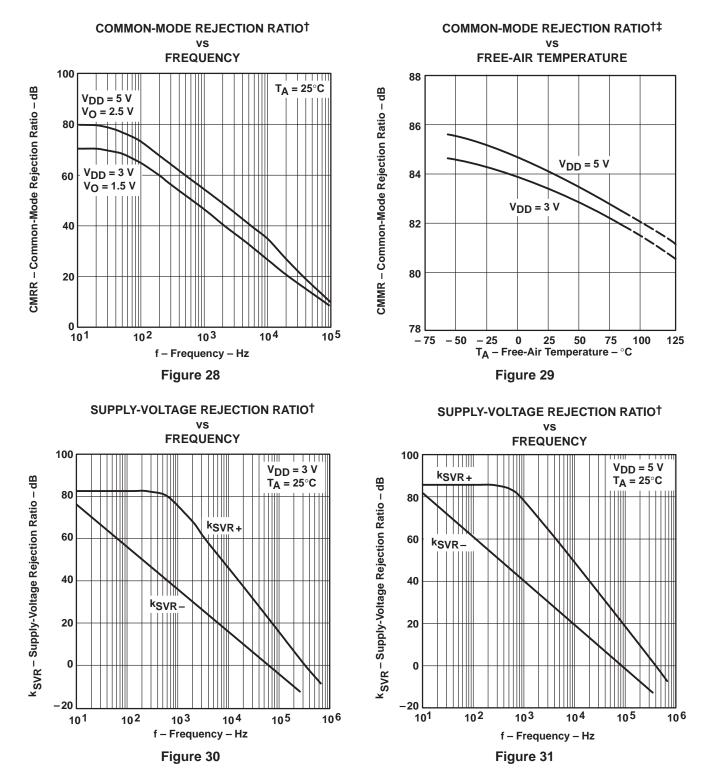


TYPICAL CHARACTERISTICS



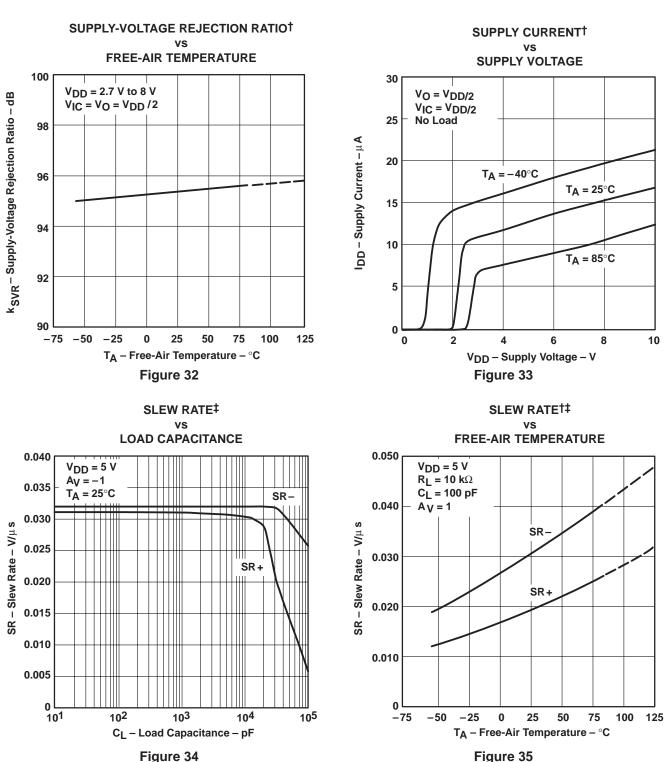


TYPICAL CHARACTERISTICS



[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V. [‡] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

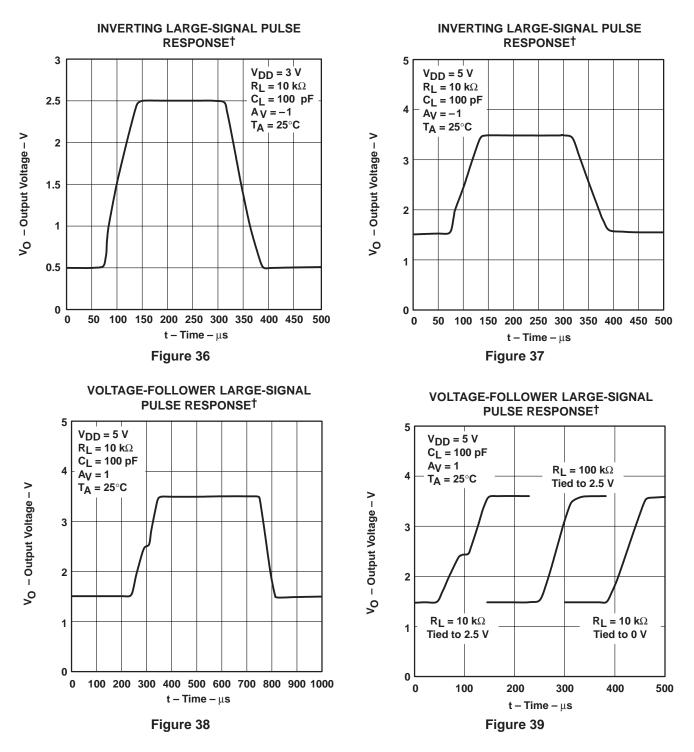




TYPICAL CHARACTERISTICS



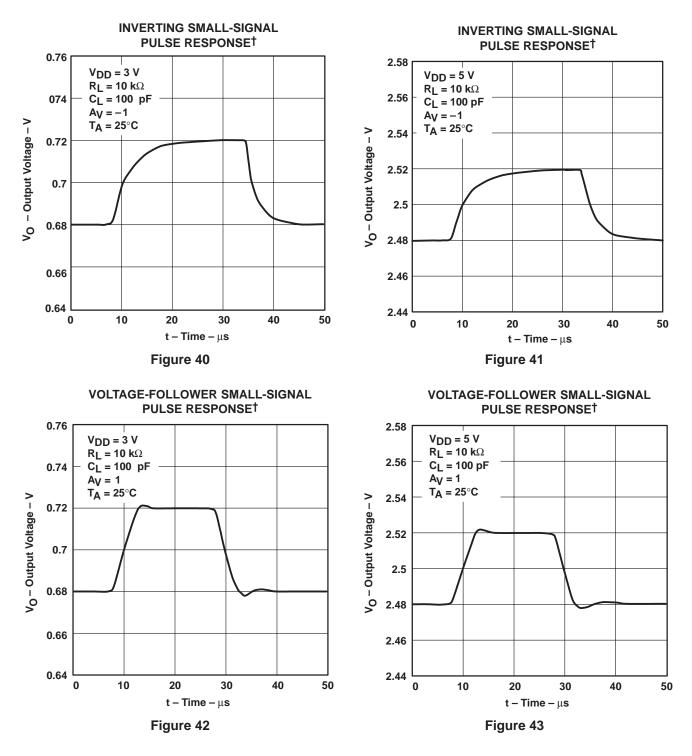
TYPICAL CHARACTERISTICS



[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



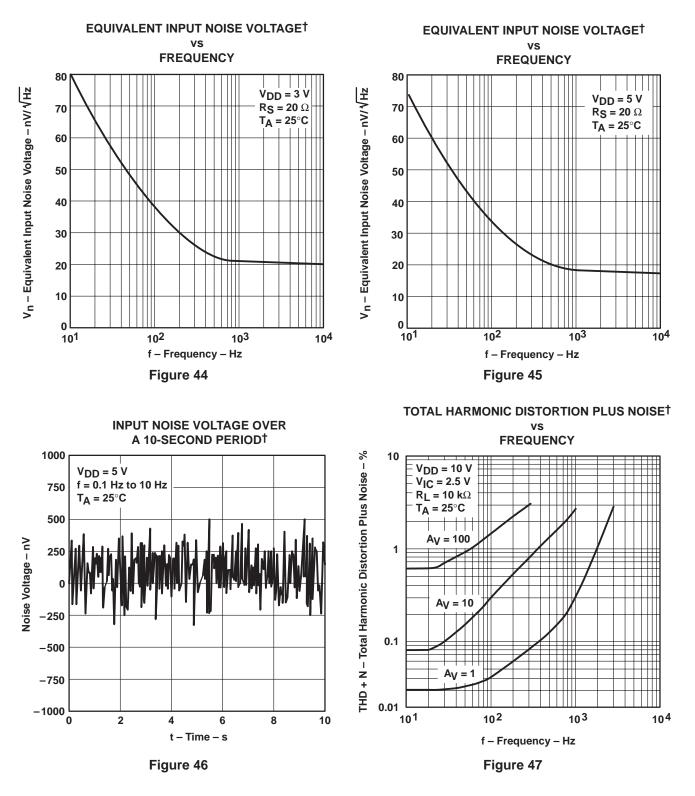
TYPICAL CHARACTERISTICS



[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



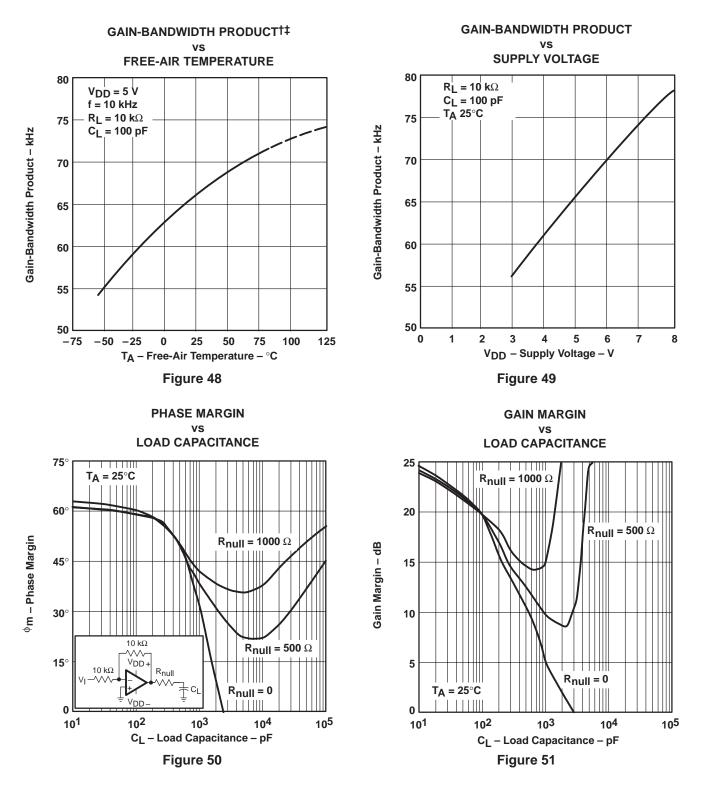
TYPICAL CHARACTERISTICS



[†] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

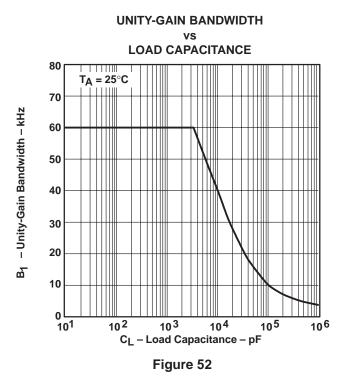


TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS



APPLICATION INFORMATION

driving large capacitive loads

The TLV2711 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 and Figure 51 illustrate its ability to drive loads up to 600 pF while maintaining good gain and phase margins $(R_{null} = 0)$.

A smaller series resistor (R_{null}) at the output of the device (see Figure 53) improves the gain and phase margins when driving large capacitive loads. Figure 50 and Figure 51 show the effects of adding series resistances of 500 Ω and 1000 Ω . The addition of this series resistor has two effects: the first is that it adds a zero to the transfer function and the second is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation 1 can be used.

$$\Delta \phi_{m1} = \tan^{-1} \left(2 \times \pi \times \text{UGBW} \times \text{R}_{\text{null}} \times \text{C}_{L} \right)$$

(1)

Where :

 $\Delta \phi_{m1}$ = Improvement in phase margin

- UGBW = Unity-gain bandwidth frequency
 - R_{null} = Output series resistance
 - $C_{I} = :$ Load capacitance



APPLICATION INFORMATION

driving large capacitive loads (continued)

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 52). To use equation 1, UGBW must be approximated from Figure 52.

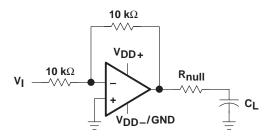


Figure 53. Series-Resistance Circuit

driving heavy dc loads

The TLV2711 is designed to provide better sinking and sourcing output currents than earlier CMOS rail-to-rail output devices. This device is specified to sink 500 μ A and source 250 μ A at V_{DD} = 3 V and V_{DD} = 5 V at a maximum quiescent I_{DD} of 25 μ A. This provides a greater than 90% power efficiency.

When driving heavy dc loads, such as $10 \text{ k}\Omega$, the positive edge under slewing conditions can experience some distortion. This condition can be seen in Figure 38. This condition is affected by three factors.

- Where the load is referenced. When the load is referenced to either rail, this condition does not occur. The distortion occurs only when the output signal swings through the point where the load is referenced. Figure 39 illustrates two 10-kΩ load conditions. The first load condition shows the distortion seen for a 10-kΩ load tied to 2.5 V. The third load condition shows no distortion for a 10-kΩ load tied to 0 V.
- Load resistance. As the load resistance increases, the distortion seen on the output decreases. Figure 39 illustrates the difference seen on the output for a $10 \cdot k\Omega$ load and a $100 \cdot k\Omega$ load with both tied to 2.5 V.
- Input signal edge rate. Faster input edge rates for a step input result in more distortion than with slower input edge rates.



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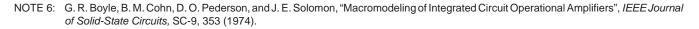
APPLICATION INFORMATION

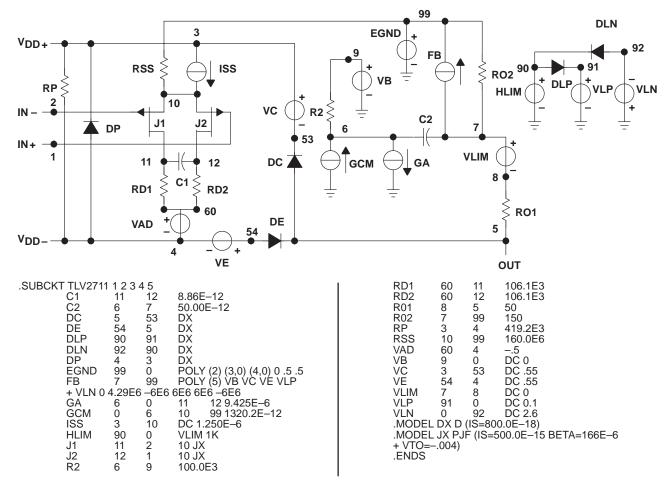
macromodel information

Macromodel information provided was derived using Microsim Parts™, the model generation software used with Microsim PSpice™. The Boyle macromodel (see Note 6) and subcircuit in Figure 54 are generated using the TLV2711 typical electrical and operating characteristics at $T_A = 25^{\circ}C$. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification

- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit







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PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package		Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material (6)	(3)		(4/5)	
TLV2711CDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VAJC	Samples
TLV2711CDBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	VAJC	Samples
TLV2711CDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		VAJC	Samples
TLV2711IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VAJI	Samples
TLV2711IDBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VAJI	Samples
TLV2711IDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		VAJI	Samples
TLV2711IDBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		VAJI	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



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PACKAGE OPTION ADDENDUM

10-Dec-2020

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2711CDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711CDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

24-Apr-2020



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2711CDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2711CDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2711IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2711IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0

DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. Refernce JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



DBV0005A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0005A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

8. Board assembly site may have different recommendations for stencil design.



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